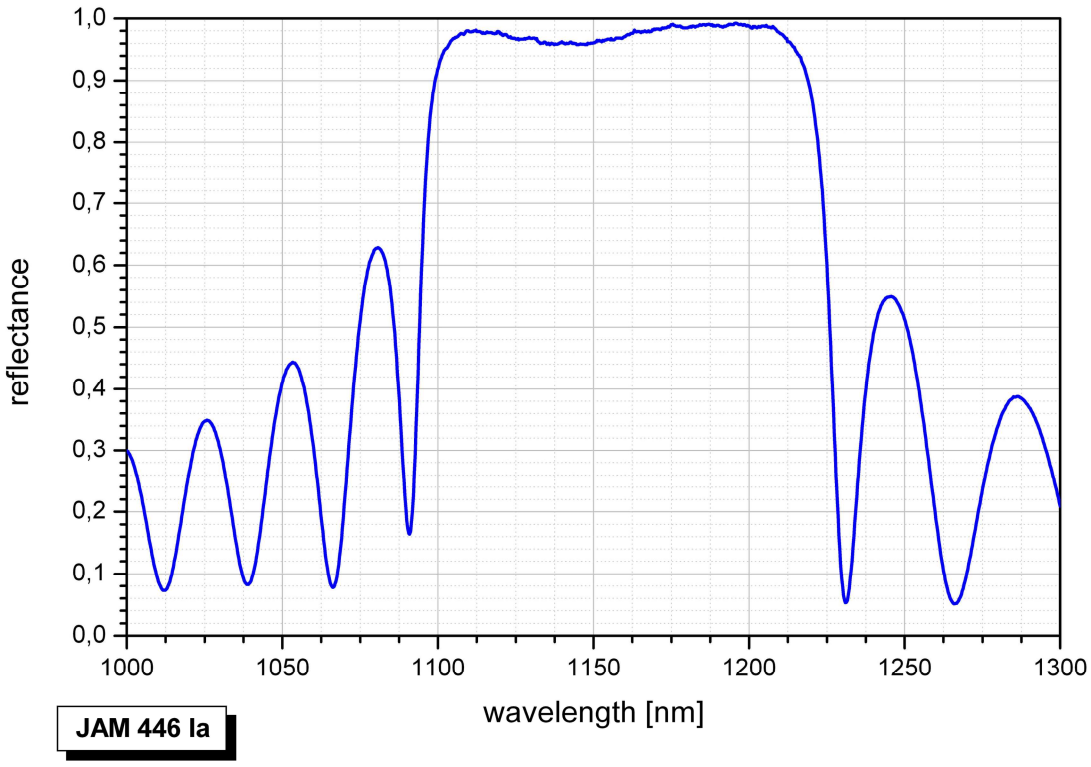
SAM™ Data Sheet SAM-1150-4-500fs-x, λ = 1150 nm

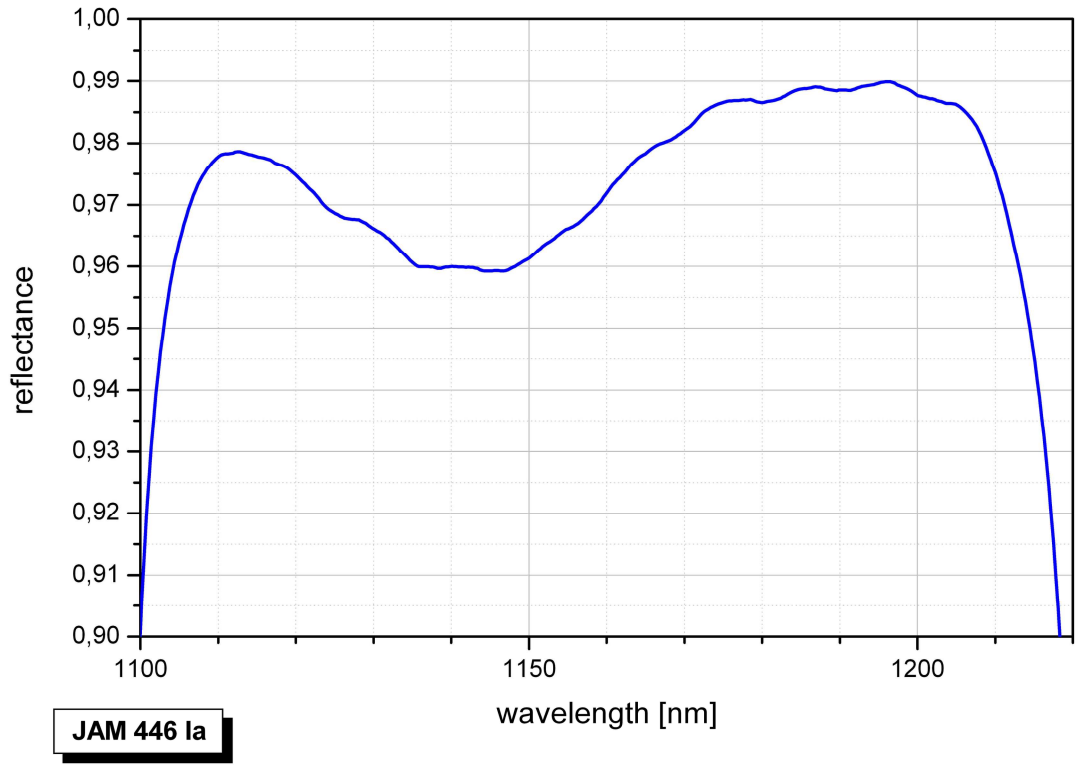
Laser wavelength	λ = 1150 nm
High reflection band	λ = 1110 .. 1200 nm
Absorptance	A_0 = 4 %
Saturation fluence	Φ_{sat} = 70 µJ/cm^2
Relaxation time constant	τ ~ 500 fs
Modulation depth	ΔR = 2.5 %
Damage threshold	Φ = 1 mJ/cm^2
Chip area	4.0 mm x 4.0 mm; other dimensions on request
Chip thickness	450 µm
Protection	the SAM is protected with a dielectric front layer

Mounting option **x** denotes the type of mounting as follows:

x = 0	unmounted
x = 12.7 g	glued on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 g	glued on a gold plated Cu-cylinder with 25.4 mm ∅
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm ∅
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm ∅

Low intensity spectral reflectance




1,00
0,99
0,98
0,97
0,96
0,95
0,94
0,93
0,92
0,91
0,90
reflectance
1100
1150
1200
wavelength [nm]
JAM 446 Ia